

NEC

SILICON TRANSISTOR
2SC4092

HIGH FREQUENCY LOW NOISE AMPLIFIER
NPN SILICON EPITAXIAL TRANSISTOR
4 PINS MINI MOLD

DESCRIPTION

The 2SC4092 is an NPN silicon epitaxial transistor designed for low-noise amplifier at VHF, UHF band.

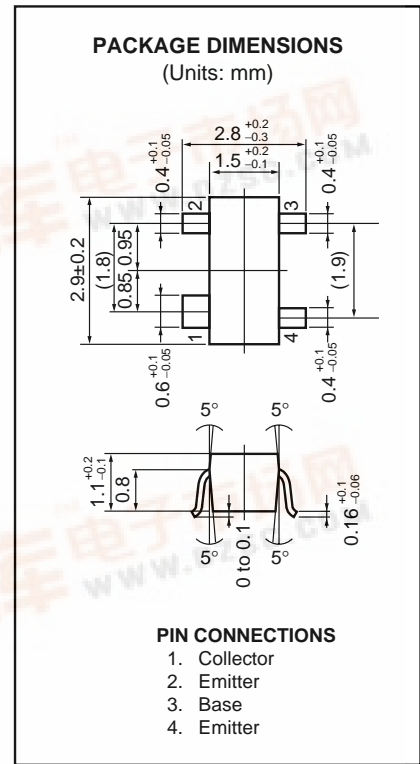
It is contained in 4 pins mini-mold package which enables high-isolation gain.

FEATURES

- NF = 1.5 dB TYP. @f = 1.0 GHz, V_{CE} = 10 V, I_c = 5 mA
- |S_{21e}|² = 12 dB TYP. @f = 1.0 GHz, V_{CE} = 10 V, I_c = 20 mA

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C)

Collector to Base Voltage	V _{CB0}	25	V
Collector to Emitter Voltage	V _{CEO}	12	V
Emitter to Base Voltage	V _{EB0}	3.0	V
Collector Current	I _c	70	mA
Total Power Dissipation	P _T	200	mW
Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	-65 to +150	°C



ELECTRICAL CHARACTERISTICS (T_A = 25 °C)

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
Collector Cutoff Current	I _{cBO}			0.1	μA	V _{CB} = 15 V, I _E = 0
Emitter Cutoff Current	I _{EBO}			0.1	μA	V _{EB} = 2.0 V, I _c = 0
DC Current Gain	h _{FE}	40		200		V _{CE} = 10 V, I _c = 20 mA
Gain Bandwidth Product	f _T		6		GHz	V _{CE} = 10 V, I _c = 20 mA f = 1.0 GHz
Output Capacitance	C _{ob}		0.55	0.9	pF	V _{CB} = 10 V, I _E = 0, f = 1.0 MHz
Insertion Power Gain	S _{21e} ²	9.5	12		dB	V _{CE} = 10 V, I _c = 20 mA, f = 1.0 GHz
Noise Figure	NF		1.5	3.0	dB	V _{CE} = 10 V, I _c = 5 mA, f = 1.0 GHz
Maximum Available Gain	MAG		14.5		dB	V _{CE} = 10 V, I _c = 20 mA, f = 1.0 GHz

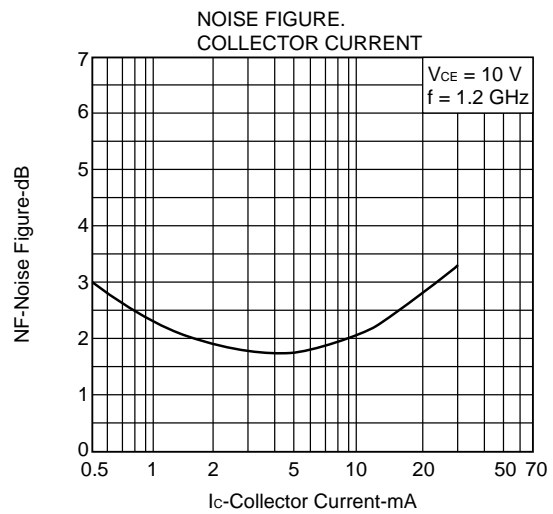
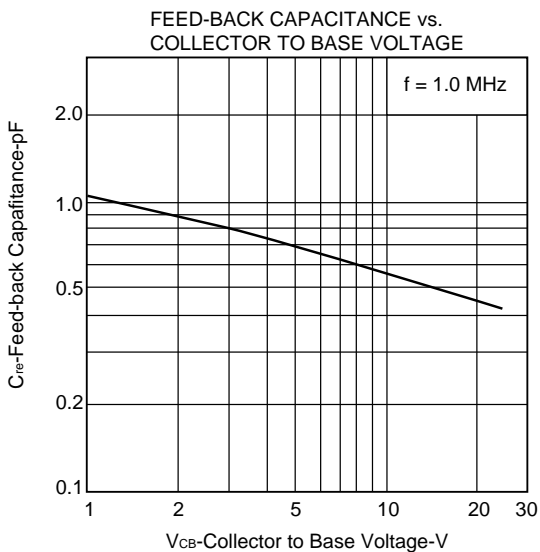
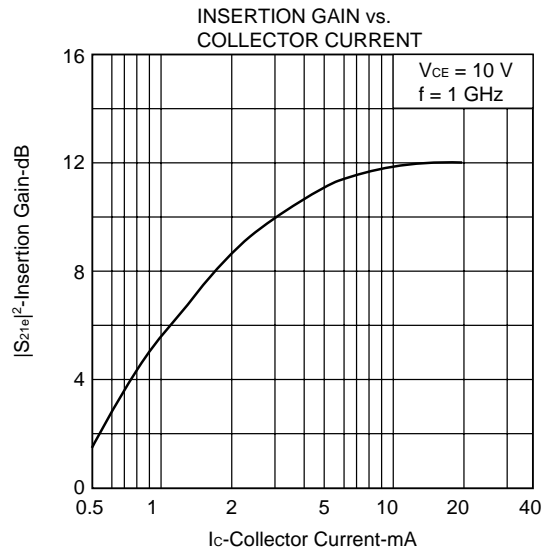
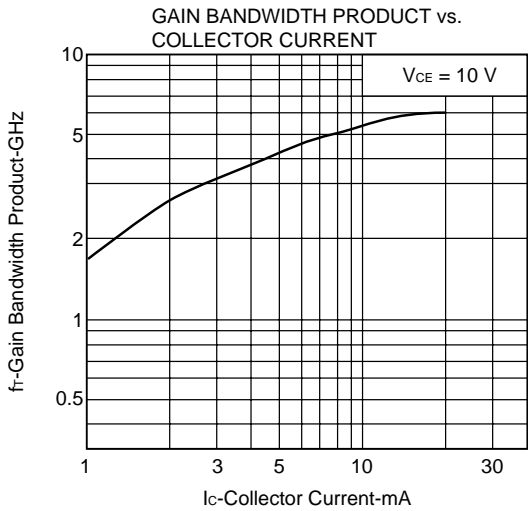
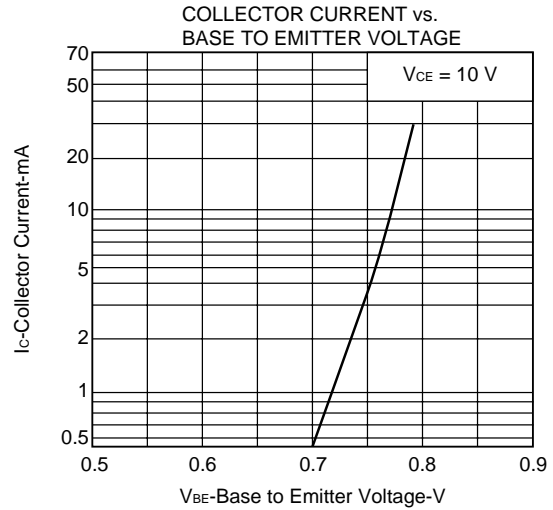
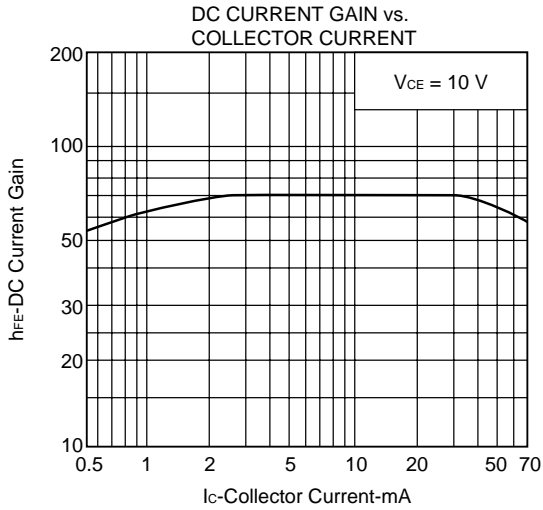
h_{FE} Classification

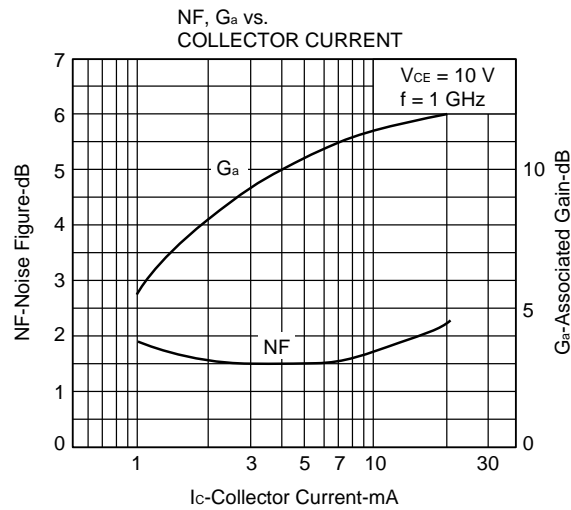
Class	R4/RD *	R5/RE *
Marking	R4	R5
h _{FE}	40 to 120	100 to 200

* Old Specification / New Specification



TYPICAL CHARACTERISTICS (T_A = 25 °C)





S-PARAMETER

$V_{CE} = 10\text{ V}$, $I_c = 5\text{ mA}$, $Z_o = 50\ \Omega$

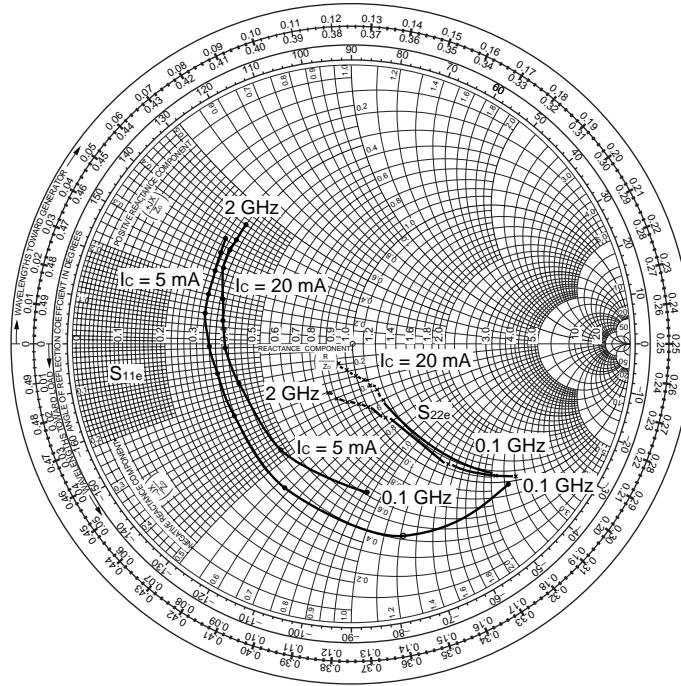
f (MHz)	$ S_{11} $	$\angle S_{11}$	$ S_{21} $	$\angle S_{21}$	$ S_{12} $	$\angle S_{12}$	$ S_{22} $	$\angle S_{22}$
100	0.780	-39.4	13.956	155.8	0.027	62.9	0.905	-21.2
200	0.709	-73.6	11.808	130.8	0.058	62.3	0.767	-36.3
400	0.567	-114.4	7.509	106.5	0.081	42.1	0.542	-50.3
600	0.503	-143.3	5.678	93.2	0.093	39.0	0.424	-56.2
800	0.486	-164.3	4.155	80.6	0.104	36.8	0.353	-59.3
1000	0.488	-179.5	3.499	72.3	0.117	37.2	0.301	-63.1
1200	0.506	167.5	2.830	63.0	0.129	36.6	0.265	-66.1
1400	0.520	159.9	2.588	55.3	0.144	35.9	0.246	-73.4
1600	0.528	149.8	2.188	48.5	0.155	37.5	0.217	-79.1
1800	0.533	141.8	2.092	41.7	0.173	35.7	0.209	-88.0
2000	0.556	134.9	1.794	36.0	0.181	36.1	0.192	-97.8

$V_{CE} = 10\text{ V}$, $I_c = 5\text{ mA}$, $Z_o = 50\ \Omega$

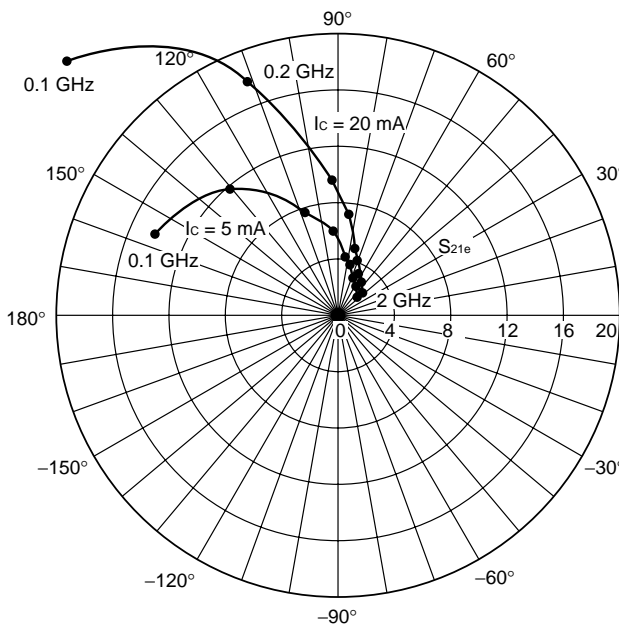
f (MHz)	$ S_{11} $	$\angle S_{11}$	$ S_{21} $	$\angle S_{21}$	$ S_{12} $	$\angle S_{12}$	$ S_{22} $	$\angle S_{22}$
100	0.534	-82.1	25.861	136.3	0.021	34.8	0.717	-41.1
200	0.468	-121.0	17.231	110.2	0.033	60.5	0.481	-50.5
400	0.428	-157.0	9.440	92.4	0.051	50.1	0.297	-57.8
600	0.435	-176.6	6.738	83.4	0.069	57.2	0.230	-59.5
800	0.448	170.0	4.823	73.7	0.090	54.6	0.197	-60.9
1000	0.464	161.0	4.013	67.2	0.107	54.1	0.164	-66.3
1200	0.480	152.1	3.232	59.4	0.127	53.5	0.140	-70.7
1400	0.495	146.5	2.945	52.7	0.149	49.6	0.131	-80.5
1600	0.511	138.9	2.480	46.9	0.164	49.5	0.104	-91.4
1800	0.517	132.7	2.364	40.9	0.187	45.2	0.104	-103.7
2000	0.546	127.0	2.024	35.9	0.197	44.3	0.094	-120.7

S-PARAMETER

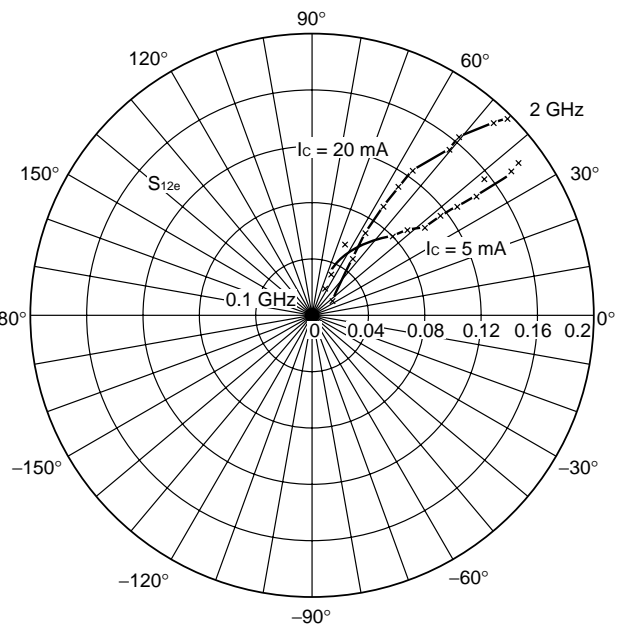
S_{11e}, S_{22e}-FREQUENCY CONDITION V_{CE} = 10 V, f = 0.1, 0.2 to 2.0 GHz (Step 200 MHz)



S_{21e}-FREQUENCY CONDITION V_{CE} = 10 V



S_{12e}-FREQUENCY CONDITION V_{CE} = 10 V



[MEMO]

[MEMO]

[MEMO]

No part of this document may be copied or reproduced in any form or by any means without the prior written consent of NEC Corporation. NEC Corporation assumes no responsibility for any errors which may appear in this document.

NEC Corporation does not assume any liability for infringement of patents, copyrights or other intellectual property rights of third parties by or arising from use of a device described herein or any other liability arising from use of such device. No license, either express, implied or otherwise, is granted under any patents, copyrights or other intellectual property rights of NEC Corporation or others.

While NEC Corporation has been making continuous effort to enhance the reliability of its semiconductor devices, the possibility of defects cannot be eliminated entirely. To minimize risks of damage or injury to persons or property arising from a defect in an NEC semiconductor device, customers must incorporate sufficient safety measures in its design, such as redundancy, fire-containment, and anti-failure features.

NEC devices are classified into the following three quality grades:

"Standard", "Special", and "Specific". The Specific quality grade applies only to devices developed based on a customer designated "quality assurance program" for a specific application. The recommended applications of a device depend on its quality grade, as indicated below. Customers must check the quality grade of each device before using it in a particular application.

Standard: Computers, office equipment, communications equipment, test and measurement equipment, audio and visual equipment, home electronic appliances, machine tools, personal electronic equipment and industrial robots

Special: Transportation equipment (automobiles, trains, ships, etc.), traffic control systems, anti-disaster systems, anti-crime systems, safety equipment and medical equipment (not specifically designed for life support)

Specific: Aircrafts, aerospace equipment, submersible repeaters, nuclear reactor control systems, life support systems or medical equipment for life support, etc.

The quality grade of NEC devices is "Standard" unless otherwise specified in NEC's Data Sheets or Data Books. If customers intend to use NEC devices for applications other than those specified for Standard quality grade, they should contact an NEC sales representative in advance.

Anti-radioactive design is not implemented in this product.